

**Session Code [09] MoJ2**

<b>Session Title</b>	Power Semiconductor Materials and Devices 2
<b>Date and Time</b>	Monday, October 4, 2021 / 13:50-15:05
<b>Session Room</b>	Room J (401)
<b>Session Chair(s)</b>	Ho-Young Cha (Hongik Univ., Korea)

**[[09] MoJ2-1] Invited Talk****[Online] 13:50-14:15****Carbon-Based Wide Band Gap-Semiconductors for Neutron Detection**

Laurent Ottaviani, Olivier Palais, Valentin Valero, Christelle Reynard-Carette (*Aix-Marseille Univ., France*), Christophe Destouches, and Abdallah Lyoussi (*CEA/DES/IRESENE, France*)

**[[09] MoJ2-2] Invited Talk****14:15-14:40****Structural and Electronic Properties of Orientation Mediated Crystal Defects in Ga<sub>2</sub>O<sub>3</sub> Homoepitaxy**

Ngo Si Trong (*Chungnam Nat'l Univ., Korea*), Hyeon Woo Kim, Sung Beom Cho (*KICET, Korea*), Young Heon Kim, Nguyen Quoc Vuong (*Chungnam Nat'l Univ., Korea*), Hu Young Jeong (*UNIST, Korea*), and Soon-Ku Hong (*Chungnam Nat'l Univ., Korea*)

**[[09] MoJ2-3] Invited Talk****[Online] 14:40-15:05****Prospects of Ultrawide Bandgap Materials and Devices**

Jash Mehta, Idriss Abid, and Farid Medjdoub (*CNRS-IEMN, France*)